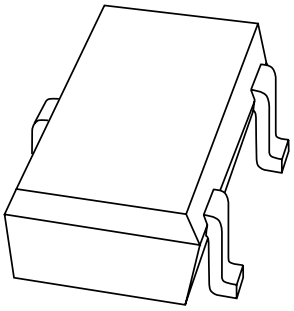
DATA SHEET



PMST3906
PNP switching transistor

Product specification
Supersedes data of 1997 May 27

1999 Apr 22

Philips
Semiconductors

PHILIPS

PNP switching transistor PMST3906

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching in telephony and professional communication equipment.

DESCRIPTION

PNP switching transistor in a SOT323 plastic package.
NPN complement: PMST3904.

MARKING

TYPE NUMBER	MARKING CODE(1)
PMST3906	∗2A

Note

1. ∗ = - : Made in Hong Kong.
   ∗ = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

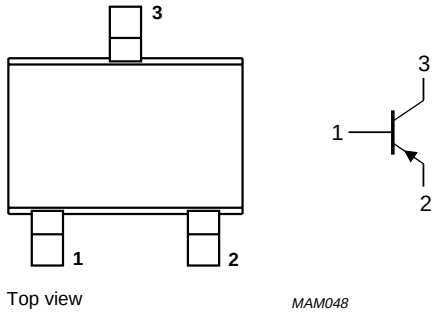


Fig.1 Simplified outline (SOT323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

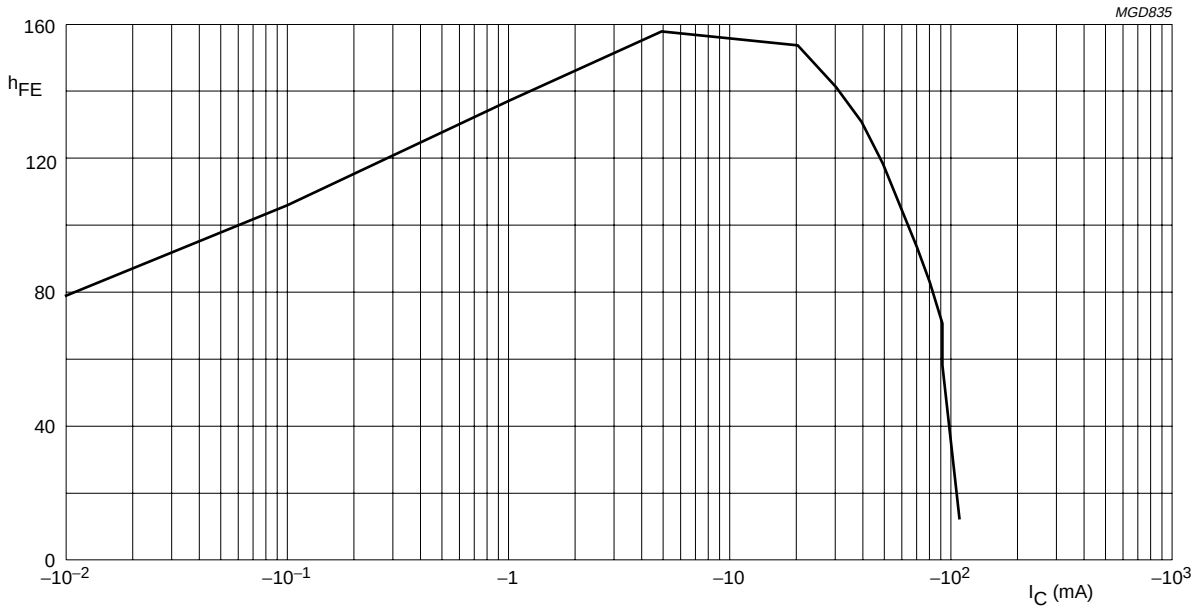
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –30 V	–	–50	nA
		I_E = 0; V_{CB} = –30 V; T_j = 150 °C	–	–10	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –6 V	–	–50	nA
h_{FE}	DC current gain	V_{CE} = –1 V; (see Fig.2)			
		I_C = –0.1 mA	60	–	
		I_C = –1 mA	80	–	
		I_C = –10 mA	100	300	
		I_C = –50 mA; note 1	60	–	
		I_C = –100 mA; note 1	30	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA; note 1	–	–200	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–	–200	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA; note 1	–	–850	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–	–950	mV
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = –5 V; f = 1 MHz	–	4.5	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = –500 mV; f = 1 MHz	–	10	pF
f_T	transition frequency	I_C = –10 mA; V_{CE} = –20 V; f = 100 MHz	250	–	MHz
F	noise figure	I_C = –100 µA; V_{CE} = –5 V; R_S = 1 kΩ; f = 10 Hz to 15.7 kHz	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.3)					
t_{on}	turn-on time	I_{Con} = –10 mA; I_{Bon} = –1 mA; I_{Boff} = 1 mA	–	65	ns
t_d	delay time		–	35	ns
t_r	rise time		–	35	ns
t_{off}	turn-off time		–	300	ns
t_s	storage time		–	225	ns
t_f	fall time		–	75	ns

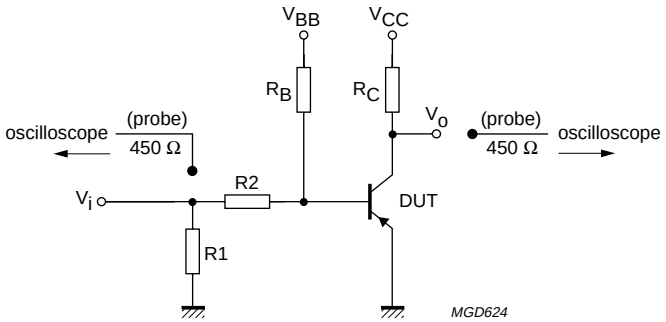
Note

1. Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.



V_{CE} = −1 V

Fig.2 DC current gain; typical values.

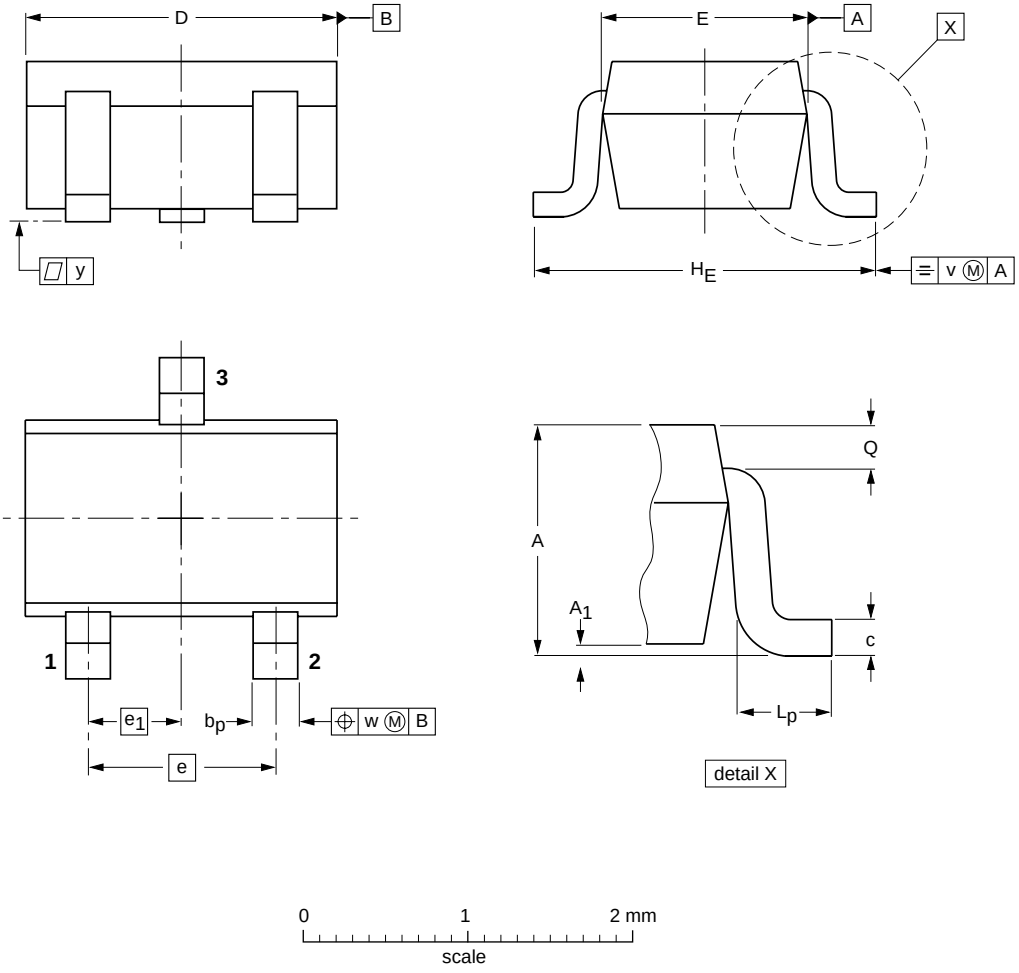


V_i = −5 V; T = 500 μs; t_p = 10 μs; t_r = t_f ≤ 3 ns.
R1 = 56 Ω; R2 = 2.5 kΩ; R_B = 3.9 kΩ; R_C = 270 Ω.
V_{BB} = 1.9 V; V_{CC} = −3 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.3 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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